

1SS119

Silicon Epitaxial Planar Diode for High Speed Switching

REJ03G0564-0300
 (Previous: ADE-208-180B)
 Rev.3.00
 Mar 23, 2005

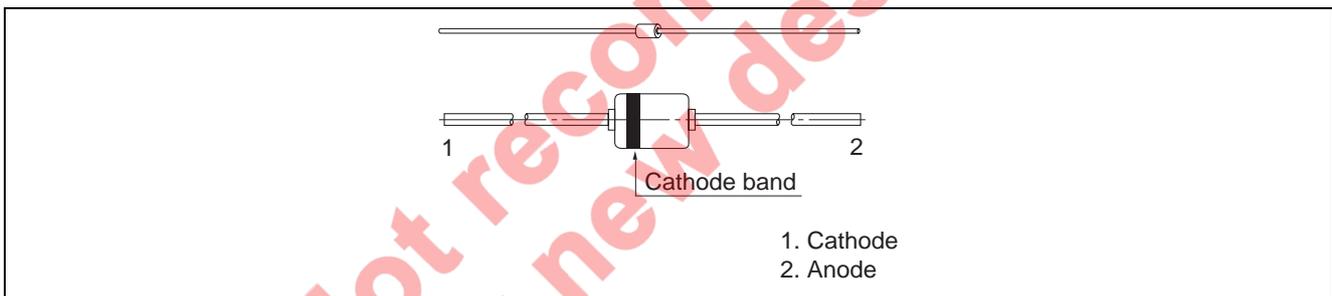
Features

- Low capacitance. ($C = 3.0 \text{ pF max}$)
- Short reverse recovery time. ($t_{rr} = 3.5 \text{ ns max}$)
- Small glass package (MHD) enables easy mounting and high reliability.

Ordering Information

Type No.	Cathode band	Package Name	Package Code (Previous Code)
1SS119	Light Blue	MHD	GRZZ0002ZC-A (MHD)

Pin Arrangement



Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Peak reverse voltage	V_{RM}	35	V
Reverse voltage	V_R	30	V
Average rectified current	I_o	150	mA
Peak forward current	I_{FM}	450	mA
Non-Repetitive peak forward surge current	I_{FSM}^*	1	A
Power dissipation	P_d	250	mW
Junction temperature	T_j	175	°C
Storage temperature	T_{stg}	-65 to +175	°C

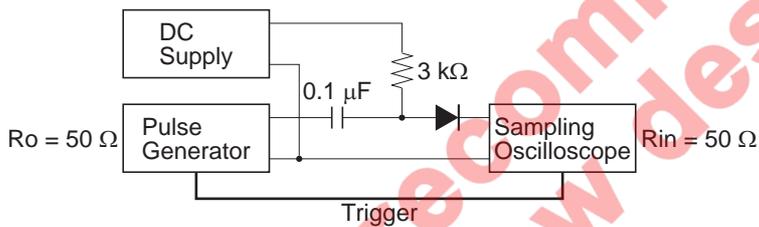
Note: * Within 1s forward surge current.

Electrical Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	0.8	V	$I_F = 10 \text{ mA}$
Reverse current	I_R	—	—	0.1	μA	$V_R = 30 \text{ V}$
Capacitance	C	—	—	3.0	pF	$V_R = 1 \text{ V}, f = 1 \text{ MHz}$
Reverse recovery time	t_{rr}^*	—	—	3.5	ns	$I_F = 10 \text{ mA}, V_R = 6 \text{ V}, R_L = 50 \Omega$

Note: Reverse recovery time test circuit



Main Characteristic

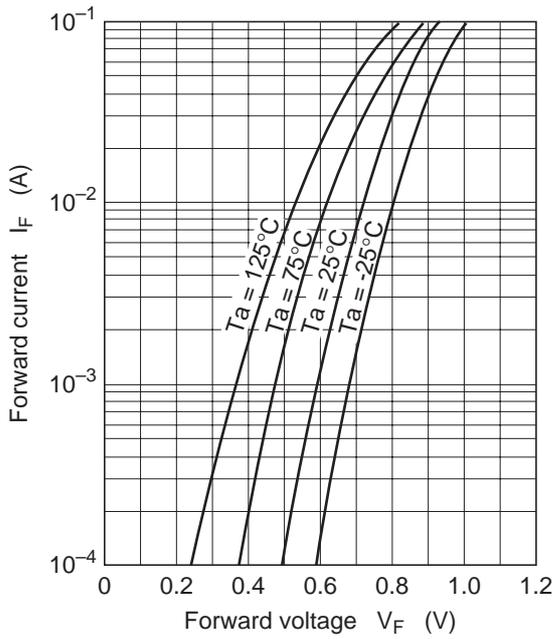


Fig.1 Forward current vs. Forward voltage

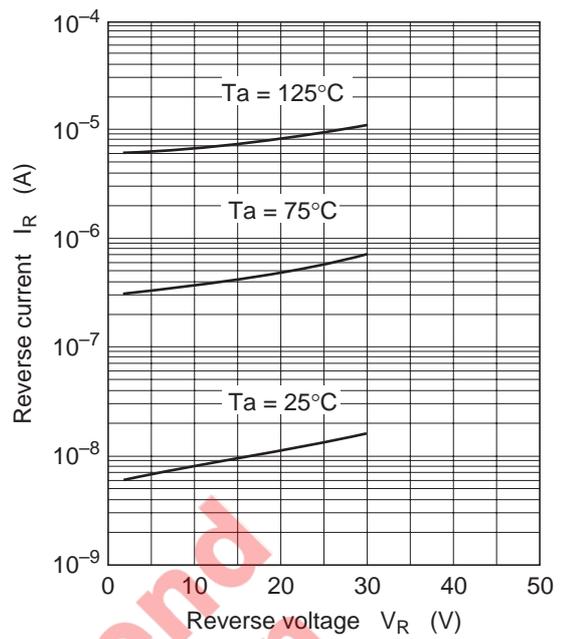


Fig.2 Reverse current vs. Reverse voltage

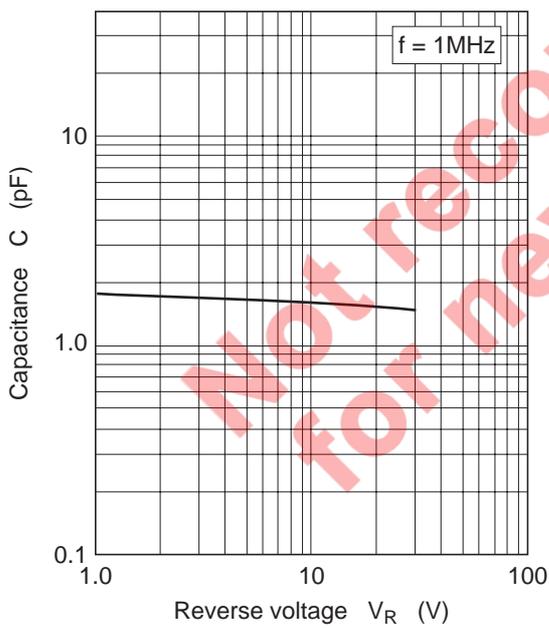
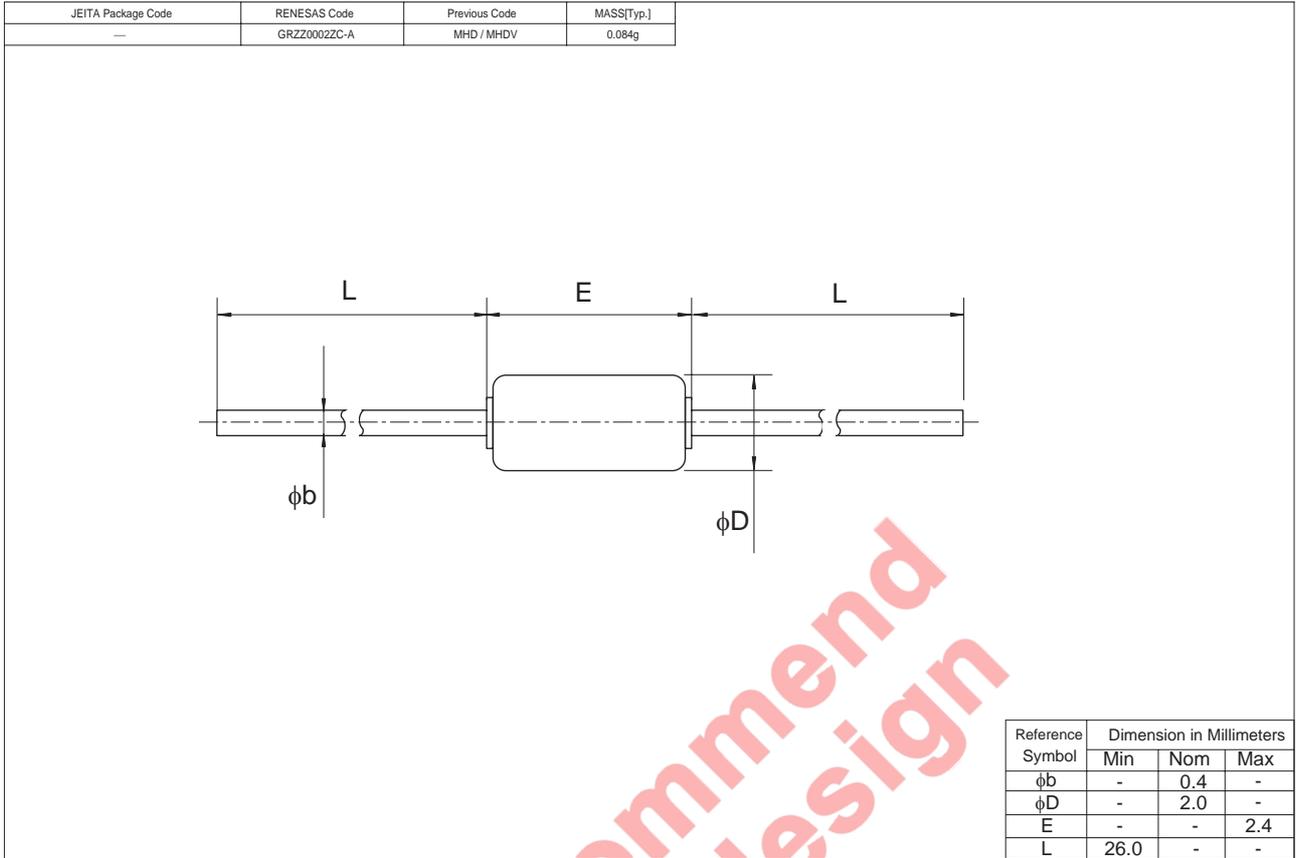


Fig.3 Capacitance vs. Reverse voltage

Package Dimensions



Not recommend for new design